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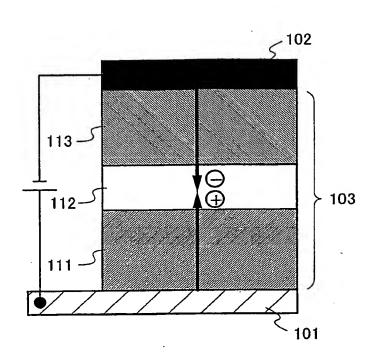
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(54) Title: LIGHT EMFTTING ELEMENT AND LIGHT EMFTTING DEVICE



(57) Abstract: The present invention provides a light-emitting element sandwiching a composite layer in which an organic compound and an inorganic compound are mixed between a first electrode and a second electrode, where the composite layer includes a first layer including a first organic compound and a first inorganic compound that exhibits an electron accepting property to the first organic compound (serves as an electron acceptor), a second layer including a second organic compound and a second inorganic compound, and a third layer including a third organic compound and a third inorganic compound that exhibits an electron donating property to the third organic compound (serves as an electron acceptor).

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